

Dong Yeong Kim

List of Publications by Year in descending order

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Version: 2024-02-01

25
papers

1,038
citations

623188

14
h-index

713013

21
g-index

26
all docs

26
docs citations

26
times ranked

2115
citing authors

#	ARTICLE	IF	CITATIONS
1	Efficient photoelectrochemical hydrogen production from bismuth vanadate-decorated tungsten trioxide helix nanostructures. <i>Nature Communications</i> , 2014, 5, 4775.	5.8	367
2	Tailoring Binding Abilities by Incorporating Oxophilic Transition Metals on 3D Nanostructured Ni Arrays for Accelerated Alkaline Hydrogen Evolution Reaction. <i>Journal of the American Chemical Society</i> , 2021, 143, 1399-1408.	6.6	161
3	Overcoming the fundamental light-extraction efficiency limitations of deep ultraviolet light-emitting diodes by utilizing transverse-magnetic-dominant emission. <i>Light: Science and Applications</i> , 2015, 4, e263-e263.	7.7	108
4	Enhanced overall efficiency of GaInN-based light-emitting diodes with reduced efficiency droop by Al-composition-graded AlGaIn/GaN superlattice electron blocking layer. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	60
5	Fundamental Limitations of Wide-Bandgap Semiconductors for Light-Emitting Diodes. <i>ACS Energy Letters</i> , 2018, 3, 655-662.	8.8	48
6	Arrays of Truncated Cone AlGaIn Deep-Ultraviolet Light-Emitting Diodes Facilitating Efficient Outcoupling of in-Plane Emission. <i>ACS Photonics</i> , 2016, 3, 2030-2034.	3.2	47
7	An elegant route to overcome fundamentally-limited light extraction in AlGaIn deep-ultraviolet light-emitting diodes: Preferential outcoupling of strong in-plane emission. <i>Scientific Reports</i> , 2016, 6, 22537.	1.6	46
8	Wafer-scale and selective-area growth of high-quality hexagonal boron nitride on Ni(111) by metal-organic chemical vapor deposition. <i>Scientific Reports</i> , 2019, 9, 5736.	1.6	42
9	Three-Dimensional Nanostructured Indium-Tin-Oxide Electrodes for Enhanced Performance of Bulk Heterojunction Organic Solar Cells. <i>Advanced Energy Materials</i> , 2014, 4, 1301566.	10.2	27
10	Pressure-Dependent Growth of Wafer-Scale Few-layer h-BN by Metal-Organic Chemical Vapor Deposition. <i>Crystal Growth and Design</i> , 2017, 17, 2569-2575.	1.4	21
11	Improvements in structural and optical properties of wafer-scale hexagonal boron nitride film by post-growth annealing. <i>Scientific Reports</i> , 2019, 9, 10590.	1.6	21
12	Role of hydrogen carrier gas on the growth of few layer hexagonal boron nitrides by metal-organic chemical vapor deposition. <i>AIP Advances</i> , 2017, 7, .	0.6	20
13	Correlative High-Resolution Mapping of Strain and Charge Density in a Strained Piezoelectric Multilayer. <i>Advanced Materials Interfaces</i> , 2015, 2, 1400281.	1.9	18
14	Resistive Switching in Few-Layer Hexagonal Boron Nitride Mediated by Defects and Interfacial Charge Transfer. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 46288-46295.	4.0	18
15	Defect-Mediated In-Plane Electrical Conduction in Few-Layer sp ² -Hybridized Boron Nitrides. <i>ACS Applied Materials & Interfaces</i> , 2018, 10, 17287-17294.	4.0	10
16	Strong correlation between capacitance and breakdown voltage of GaInN/GaN light-emitting diodes. <i>Electronic Materials Letters</i> , 2014, 10, 1155-1157.	1.0	6
17	Polarization-Engineered High-Efficiency GaInN Light-Emitting Diodes Optimized by Genetic Algorithm. <i>IEEE Photonics Journal</i> , 2015, 7, 1-9.	1.0	6
18	Thermal laser evaporation for the growth of oxide films. <i>APL Materials</i> , 2021, 9, .	2.2	4

#	ARTICLE	IF	CITATIONS
19	Electron Holography: Correlative High-Resolution Mapping of Strain and Charge Density in a Strained Piezoelectric Multilayer (Adv. Mater. Interfaces 1/2015). Advanced Materials Interfaces, 2015, 2, .	1.9	3
20	Epitaxial film growth by thermal laser evaporation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	3
21	Counter-intuitive junction temperature behavior in AlGaIn-based deep-ultraviolet light-emitting diodes. AIP Advances, 2020, 10, 045135.	0.6	2
22	Modulation of hole-injection in GaInN-light emitting triodes and its effect on carrier recombination behavior. AIP Advances, 2015, 5, 107104.	0.6	0
23	U-shape phenomenon in the efficiency-versus-current curves in AlGaIn-based deep-ultraviolet light-emitting diodes. , 2015, , .		0
24	Enhanced light extraction efficiency of AlGaIn-based deep-ultraviolet light-emitting diodes by utilizing strong sidewall emission. , 2015, , .		0
25	Effects of electrochemical potentiostatic activation on carrier transport in AlGaIn-based deep-ultraviolet light-emitting diodes. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, 023410.	0.9	0